REMARKS

No new matter has been added. The Applicants again request entry of the amendments as set forth in the Appendices hereto prior to examination of the application on the merits.

Respectfully submitted,

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Enclosure: Version of Claims With Markings to Show Changes Made

VERSION OF CLAIMS WITH MARKINGS TO SHOW CHANGES MADE

3. (Amended) The semiconductor processing assembly of claim 1, wherein [the] said at least one temperature sensor is configured to [sens] sense a temperature within said reaction chamber.

4. (Amended) The semiconductor processing assembly of claim 1, wherein said at least one temperature sensor is configured to sense a temperature of at least an area of [the] said at least one semiconductor substrate.

13. (Amended) The semiconductor processing assembly of claim 12, wherein said rotator is configured to rotate [the] said at least one semiconductor substrate.

14. (Amended) A supplement to a fabrication chamber configured to perform a deposition process on a substrate, [the] said supplement comprising:

a variable substrate temperature generation system configured to operate in cooperation with initiation of [the] said deposition process, said variable substrate temperature generation system comprising a feedback control system in communication with at least one temperature sensor and a heating element of [the] said fabrication chamber, said feedback control system configured to cause said heating element of [the] said fabrication chamber to alter a thermal output within [the] said fabrication chamber in response to transmission of a signal from said at least one temperature sensor.

16. (Amended) An apparatus for use with a chamber that includes a heating element and is configured to perform a semiconductor fabrication process, [the] said apparatus comprising:

a temperature control system configured to communicate with [the] said heating element and to cause uneven heat distribution across a surface of a substrate positioned within [the] said chamber during a time coincident with at least a portion of said semiconductor fabrication process.

17. (Amended) The apparatus of claim 16, wherein said temperature control system is configured to cause said uneven heat distribution during a time coincident with substantially an entire time span of [the] said semiconductor fabrication process.

20. (Amended) The apparatus of claim 18, wherein said temperature control system communicates with said at least one temperature sensor configured to [sens] sense a temperature [with the] within said chamber.

21. (Amended) The apparatus of claim 18, wherein said temperature control system communicates with said at least one temperature sensor configured to sense a temperature of at least one area of at least one semiconductor substrate within [the] said chamber.